

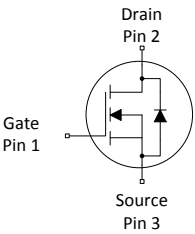
MOSFET

PG-TO220-3

OptiMOS™3 Power-Transistor, 60 V

Features

- Ideal for high frequency switching and sync. rec.
- Optimized technology for DC/DC converters
- Excellent gate charge x $R_{DS(on)}$ product (FOM)
- N-channel, normal level
- 100% avalanche tested
- Pb-free plating; RoHS compliant
- Qualified according to JEDECJ-STD20 and JESD22 for target applications

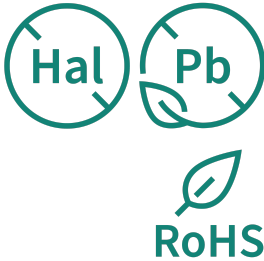


Product validation

Fully qualified according to JEDEC for Industrial Applications

Table 1 Key Performance Parameters

Parameter	Value	Unit
V_{DS}	60	V
$R_{DS(on),max}$	9.3	mΩ
I_D	43	A



Type/Ordering Code	Package	Marking	Related Links
IPA093N06N3 G	PG-TO220-3	093N06N	-



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1 Maximum ratings

at $T_j=25\text{ °C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Continuous drain current	I_D	-	-	43 31	A	$T_C=25\text{ °C}$ $T_C=100\text{ °C}$
Pulsed drain current ¹⁾	$I_{D,pulse}$	-	-	172	A	$T_C=25\text{ °C}$
Avalanche energy, single pulse ²⁾	E_{AS}	-	-	43	mJ	$I_D=50\text{ A}$, $R_{GS}=25\text{ }\Omega$
Gate source voltage	V_{GS}	-20	-	20	V	-
Power dissipation	P_{tot}	-	-	33	W	$T_C=25\text{ °C}$
Operating and storage temperature	T_j, T_{stg}	-55	-	175	°C	IEC climatic category; DIN IEC 68-1: 55/175/56

¹⁾ See figure 3 for more detailed information

²⁾ See figure 13 for more detailed information

2 Thermal characteristics

Table 3 Thermal characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	4.6	K/W	-

3 Electrical characteristics

at $T_j=25\text{ °C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	60	-	-	V	$V_{GS}=0\text{ V}$, $I_D=1\text{ mA}$
Gate threshold voltage	$V_{GS(th)}$	2	3	4	V	$V_{DS}=V_{GS}$, $I_D=34\text{ }\mu\text{A}$
Zero gate voltage drain current	I_{DSS}	-	0.1 10	1 100	μA	$V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$ $V_{DS}=60\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=125\text{ °C}$
Gate-source leakage current	I_{GSS}	-	1	100	nA	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$
Drain-source on-state resistance	$R_{DS(on)}$	-	7.8	9.3	m Ω	$V_{GS}=10\text{ V}$, $I_D=40\text{ A}$
Gate resistance	R_G	-	0.9	-	Ω	-
Transconductance	g_{fs}	26	51	-	S	$ V_{DS} >2 I_D R_{DS(on)max}$, $I_D=40\text{ A}$

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	2900	3900	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Output capacitance	C_{oss}	-	640	850	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Reverse transfer capacitance	C_{rss}	-	23	-	pF	$V_{GS}=0\text{ V}$, $V_{DS}=30\text{ V}$, $f=1\text{ MHz}$
Turn-on delay time	$t_{d(on)}$	-	15	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=45\text{ A}$, $R_{G,ext}=3.5\text{ }\Omega$
Rise time	t_r	-	40	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=45\text{ A}$, $R_{G,ext}=3.5\text{ }\Omega$
Turn-off delay time	$t_{d(off)}$	-	20	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=45\text{ A}$, $R_{G,ext}=3.5\text{ }\Omega$
Fall time	t_f	-	5	-	ns	$V_{DD}=30\text{ V}$, $V_{GS}=10\text{ V}$, $I_D=45\text{ A}$, $R_{G,ext}=3.5\text{ }\Omega$

Table 6 Gate charge characteristics ³⁾

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	16	-	nC	$V_{DD}=30\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate to drain charge	Q_{gd}	-	3	-	nC	$V_{DD}=30\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Switching charge	Q_{sw}	-	10	-	nC	$V_{DD}=30\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate charge total	Q_g	-	36	48	nC	$V_{DD}=30\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Gate plateau voltage	$V_{plateau}$	-	5.5	-	V	$V_{DD}=30\text{ V}$, $I_D=40\text{ A}$, $V_{GS}=0\text{ to }10\text{ V}$
Output charge	Q_{oss}	-	29	38	nC	$V_{DD}=30\text{ V}$, $V_{GS}=0\text{ V}$

³⁾ See "Gate charge waveforms" for parameter definition

Table 7 Reverse diode

Parameter	Symbol	Values			Unit	Note/ Test Condition
		Min.	Typ.	Max.		
Diode continuous forward current	I_S	-	-	27	A	$T_C=25\text{ °C}$
Diode pulse current	$I_{S,pulse}$	-	-	172	A	$T_C=25\text{ °C}$
Diode forward voltage	V_{SD}	-	1.0	1.2	V	$V_{GS}=0\text{ V}$, $I_F=40\text{ A}$, $T_J=25\text{ °C}$
Reverse recovery time	t_{rr}	-	45	-	ns	$V_R=30\text{ V}$, $I_F=45\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$
Reverse recovery charge	Q_{rr}	-	40	-	nC	$V_R=30\text{ V}$, $I_F=45\text{ A}$, $di_F/dt=100\text{ A}/\mu\text{s}$

4 Electrical characteristics diagrams

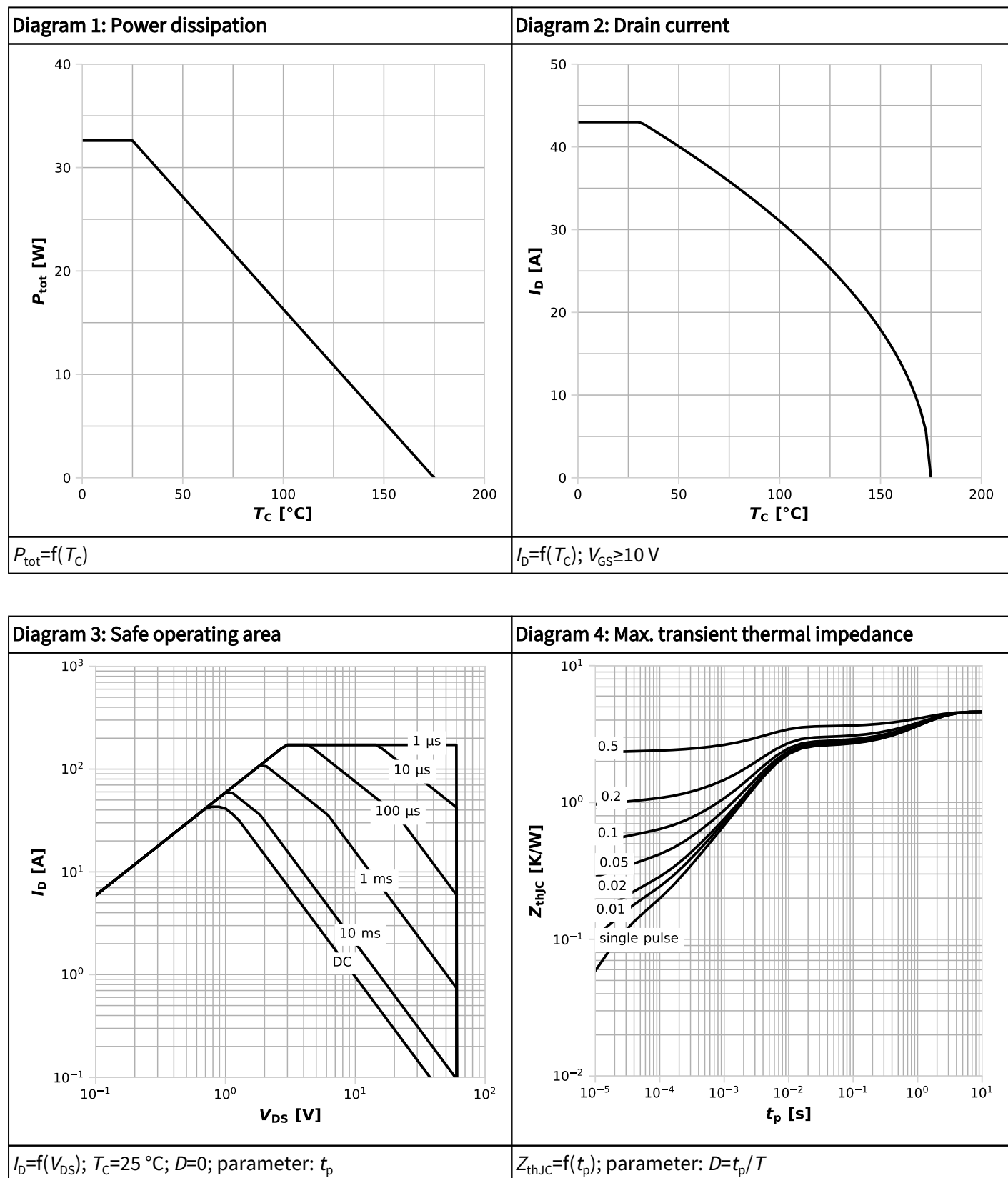
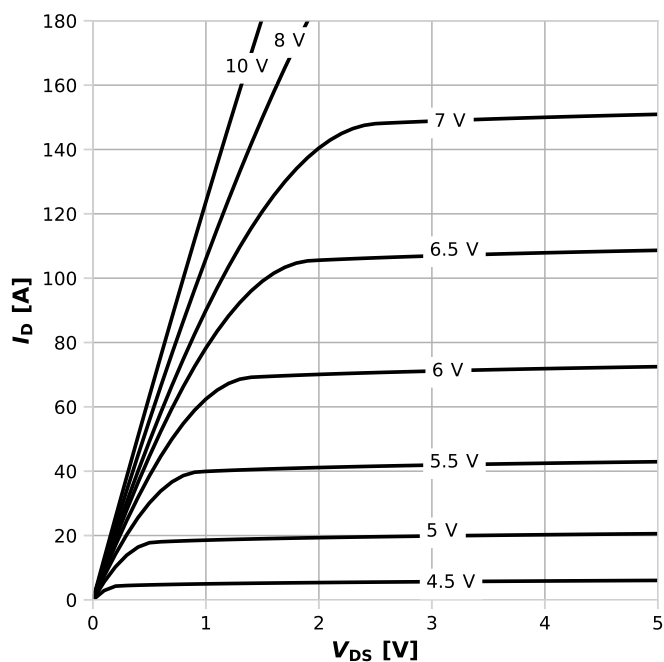
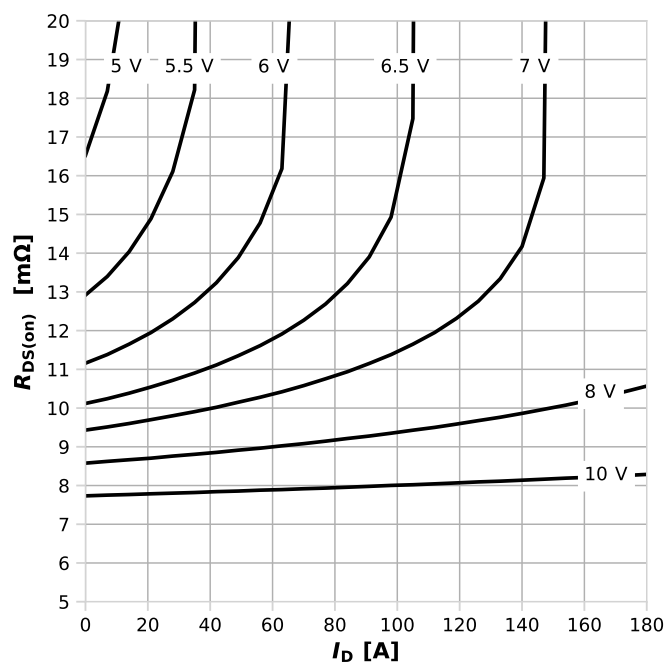


Diagram 5: Typ. output characteristics



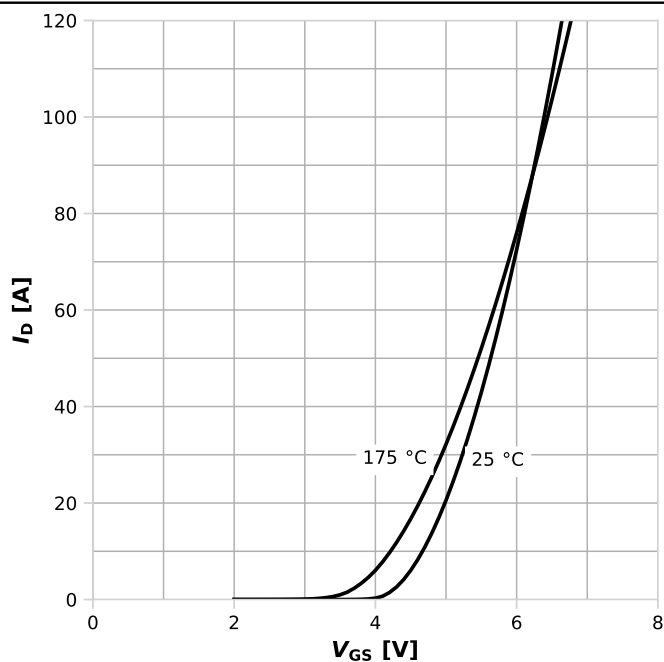
$I_D = f(V_{DS})$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 6: Typ. drain-source on resistance



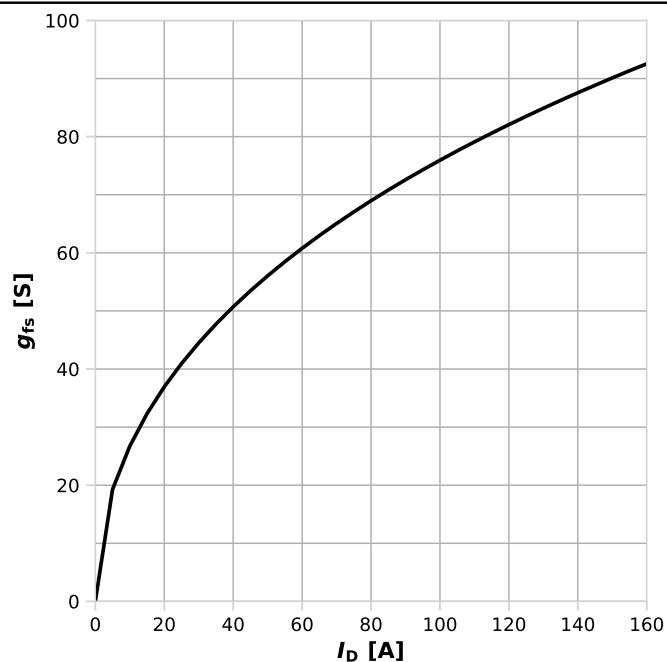
$R_{DS(on)} = f(I_D)$; $T_j = 25^\circ\text{C}$; parameter: V_{GS}

Diagram 7: Typ. transfer characteristics



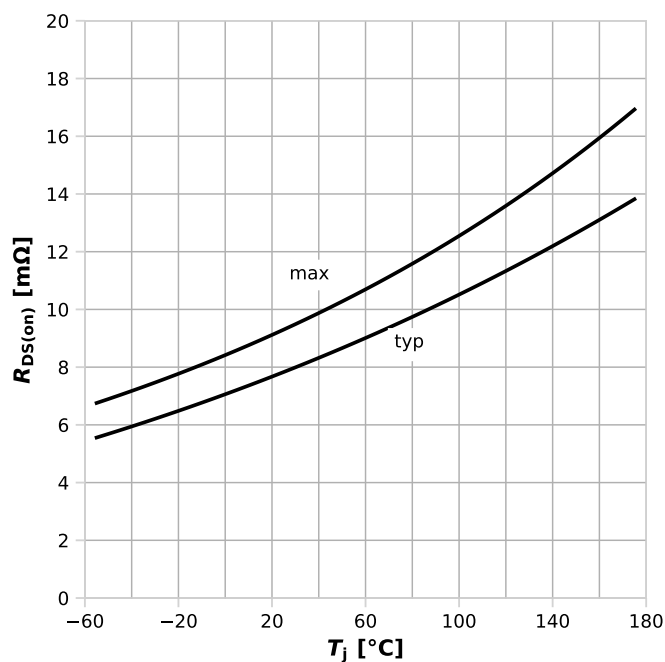
$I_D = f(V_{GS})$; $|V_{DS}| > 2|I_D|R_{DS(on)max}$; parameter: T_j

Diagram 8: Typ. forward transconductance



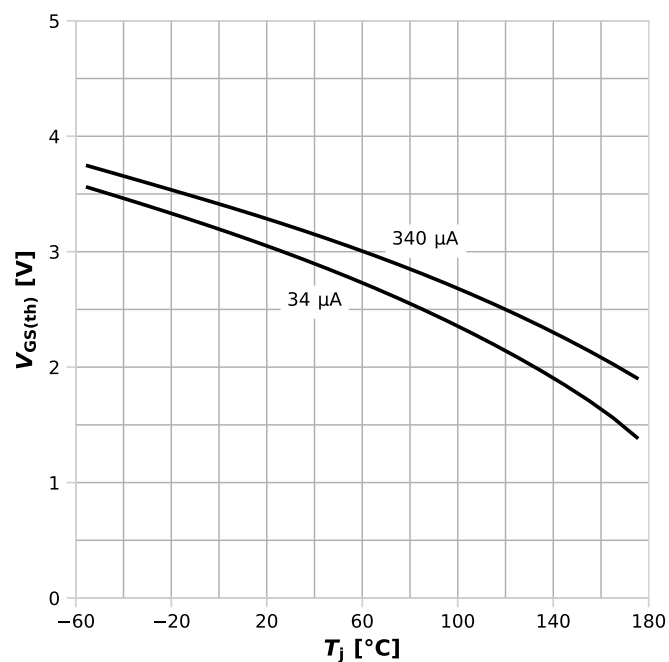
$g_{fs} = f(I_D)$; $T_j = 25^\circ\text{C}$

Diagram 9: Drain-source on-state resistance



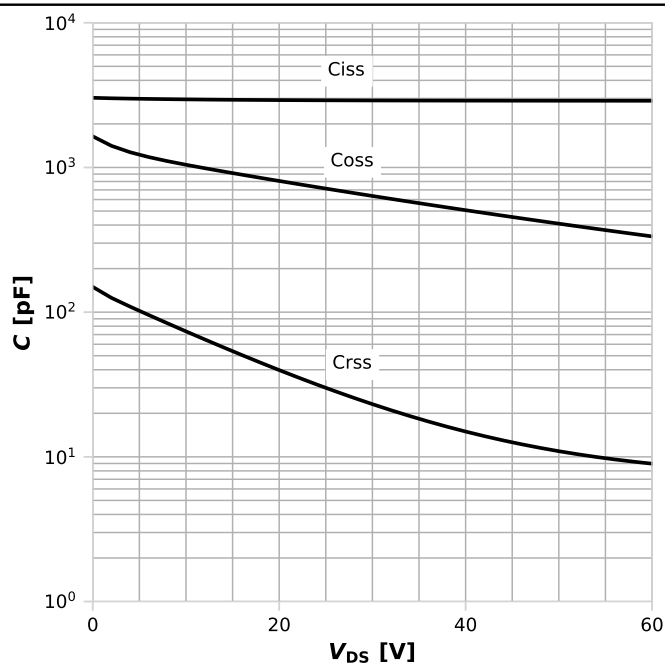
$$R_{DS(on)} = f(T_j); I_D = 40 \text{ A}; V_{GS} = 10 \text{ V}$$

Diagram 10: Typ. gate threshold voltage



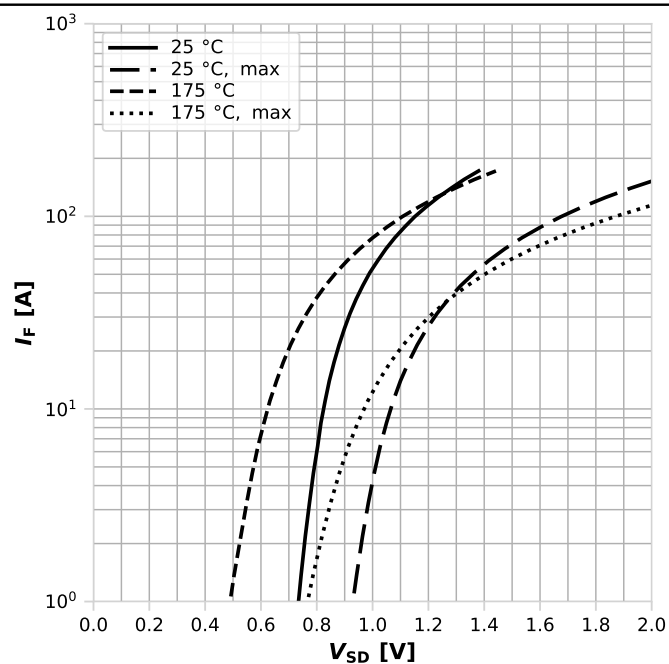
$$V_{GS(th)} = f(T_j); V_{GS} = V_{DS}; \text{parameter: } I_D$$

Diagram 11: Typ. capacitances



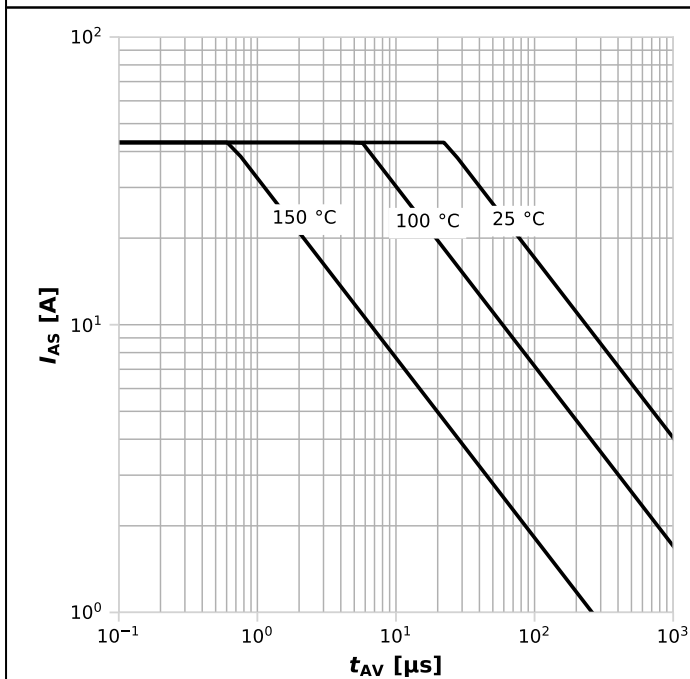
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$$

Diagram 12: Forward characteristics of reverse diode



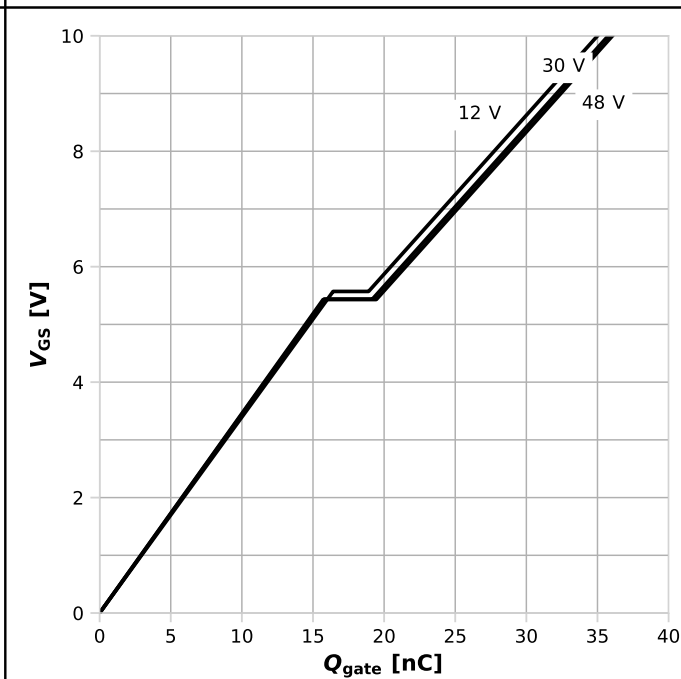
$$I_F = f(V_{SD}); \text{parameter: } T_j$$

Diagram 13: Avalanche characteristics



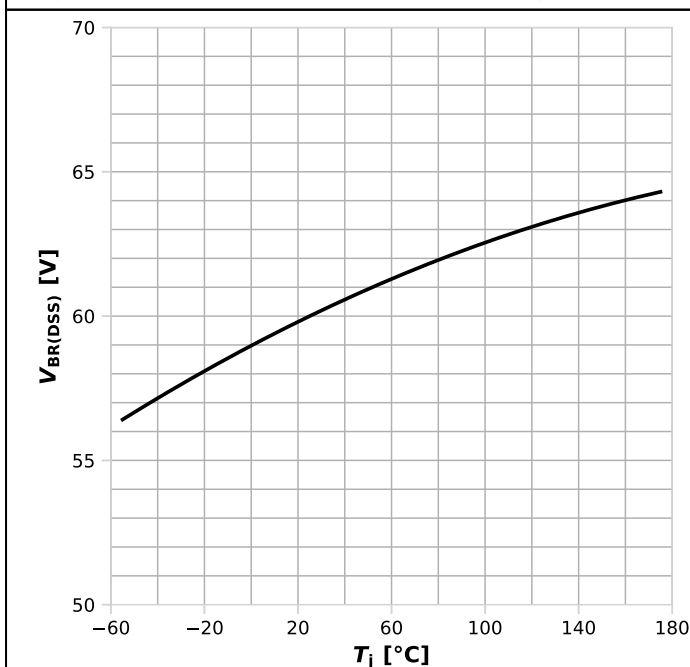
$I_{AS}=f(t_{AV})$; $R_{GS}=25\ \Omega$; parameter: $T_{j(start)}$

Diagram 14: Typ. gate charge



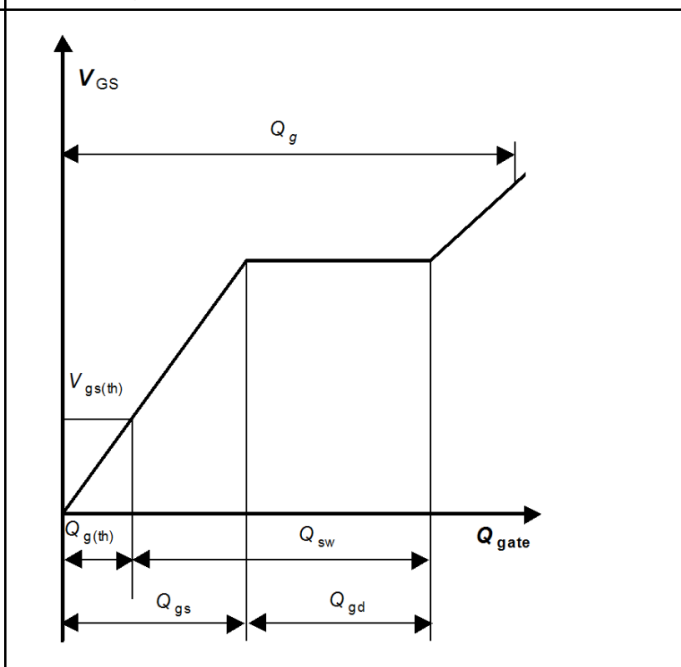
$V_{GS}=f(Q_{gate})$; $I_D=40\text{ A}$ pulsed; parameter: V_{DD}

Diagram 15: Drain-source breakdown voltage



$V_{BR(DSS)}=f(T_j)$; $I_D=1\text{ mA}$

Gate charge waveforms



-

5 Package Outlines

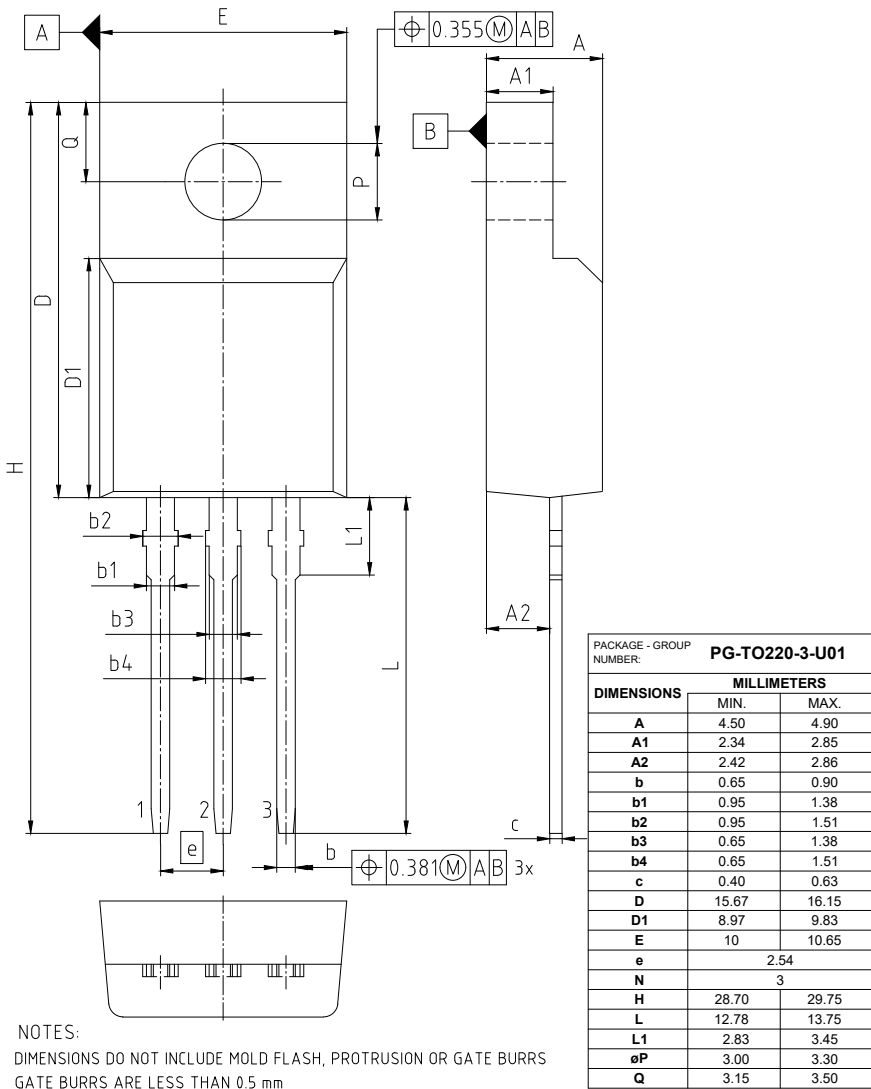


Figure 1 Outline PG-TO220-3, dimensions in mm

Revision History

IPA093N06N3 G

Revision 2024-09-11, Rev. 1.0

Previous Revision

Revision	Date	Subjects (major changes since last revision)
1.0	2024-09-11	Rev 2.2 - updated IS =27A and Diagram 12

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